

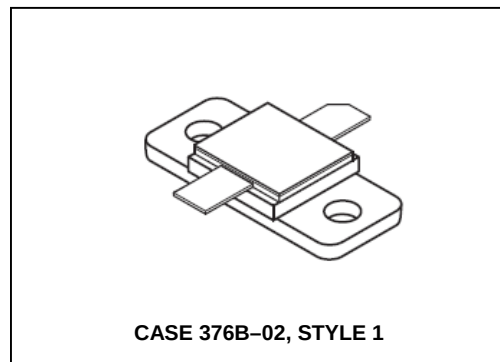
Microwave Pulse Power Silicon NPN Transistor 150W (peak), 1025–1150MHz

M/A-COM Products
Released - Rev. 07.07

Product Image

Designed for 1025–1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode-S transmitters.

- Guaranteed performance @ 1090 MHz
Output power = 150 W Peak
Gain = 9.5 dB min, 10.0 dB (typ.)
- 100% tested for load mismatch at all phase angles with 10:1 VSWR
- Hermetically sealed package
- Silicon nitride passivated
- Gold metallized, emitter ballasted for long life and resistance to metal migration
- Internal input and output matching
- Characterized with 10 μ s, 10% duty cycle pulses
- Recommended driver for a pair of MRF10500 transistors



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	65	Vdc
Collector–Base Voltage	V_{CBO}	65	Vdc
Emitter–Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Peak (1)	I_C	14	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1), (2) Derate above 25°C	P_D	700 4.0	Watts $\text{W}/^\circ\text{C}$
Storage Temperature Range	T_{stg}	–65 to +200	$^\circ\text{C}$
Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.25	$^\circ\text{C}/\text{W}$

NOTES:

1. Under pulse RF operating conditions.
2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @ 10 μ s, 10%.)

Microwave Pulse Power Silicon NPN Transistor
150W (peak), 1025–1150MHz

M/A-COM Products
Released - Rev. 07.07

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	65	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	65	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 36 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	25	mAdc

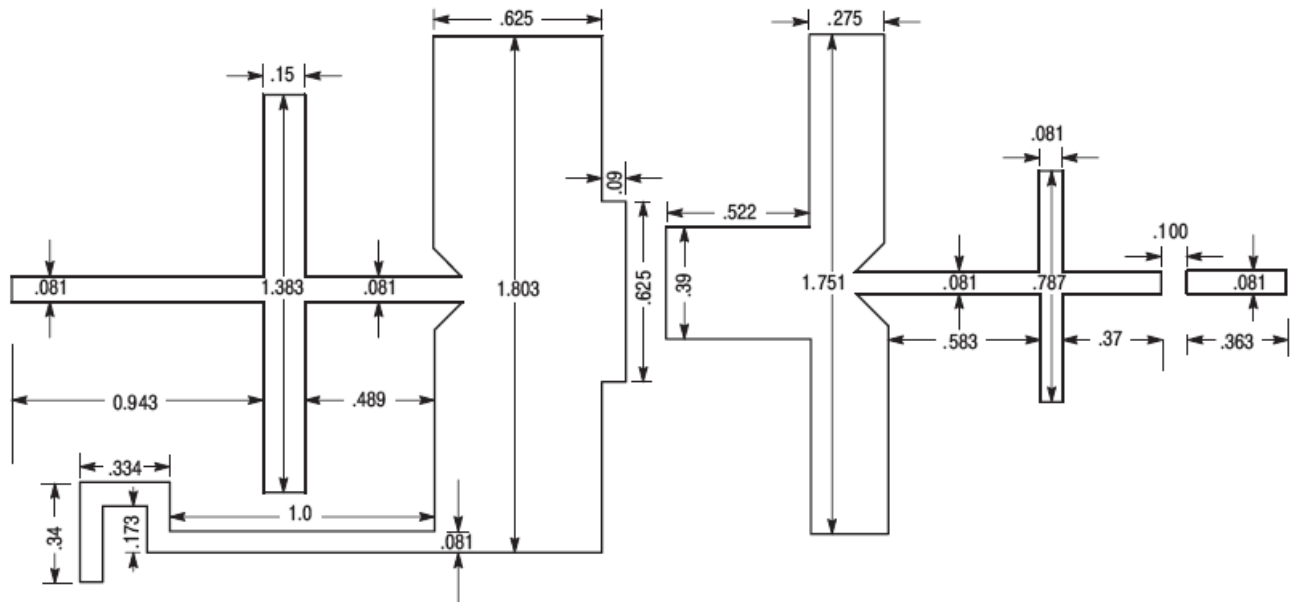
ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20	—	—	—
--	----------	----	---	---	---

FUNCTIONAL TESTS

Common–Base Amplifier Power Gain ($V_{CC} = 50 \text{ Vdc}$, $P_{out} = 150 \text{ W Peak}$, $f = 1090 \text{ MHz}$)	G_{PB}	9.5	10	—	dB
Collector Efficiency ($V_{CC} = 50 \text{ Vdc}$, $P_{out} = 150 \text{ W Peak}$, $f = 1090 \text{ MHz}$)	η	40	—	—	%
Load Mismatch ($V_{CC} = 50 \text{ Vdc}$, $P_{out} = 150 \text{ W Peak}$, $f = 1090 \text{ MHz}$, $VSWR = 10:1$ All Phase Angles)	ψ	No Degradation in Output Power			

M/A-COM Products
Released - Rev. 07.07



Microwave Pulse Power Silicon NPN Transistor
150W (peak), 1025–1150MHz

M/A-COM Products
Released - Rev. 07.07

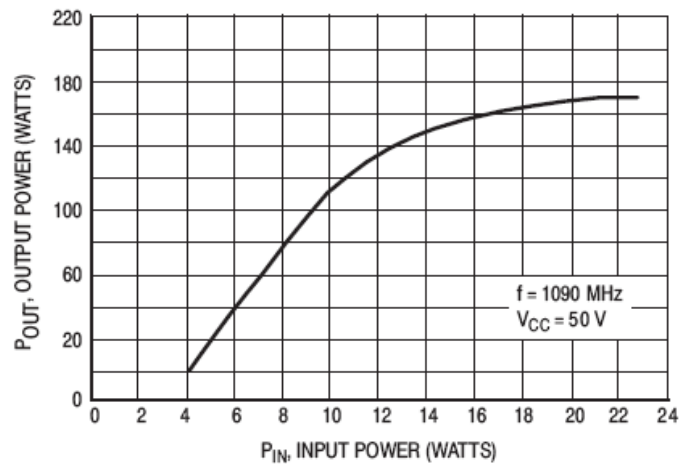


Figure 2. Output Power versus Input Power

Microwave Pulse Power Silicon NPN Transistor 150W (peak), 1025–1150MHz

M/A-COM Products
Released - Rev. 07.07

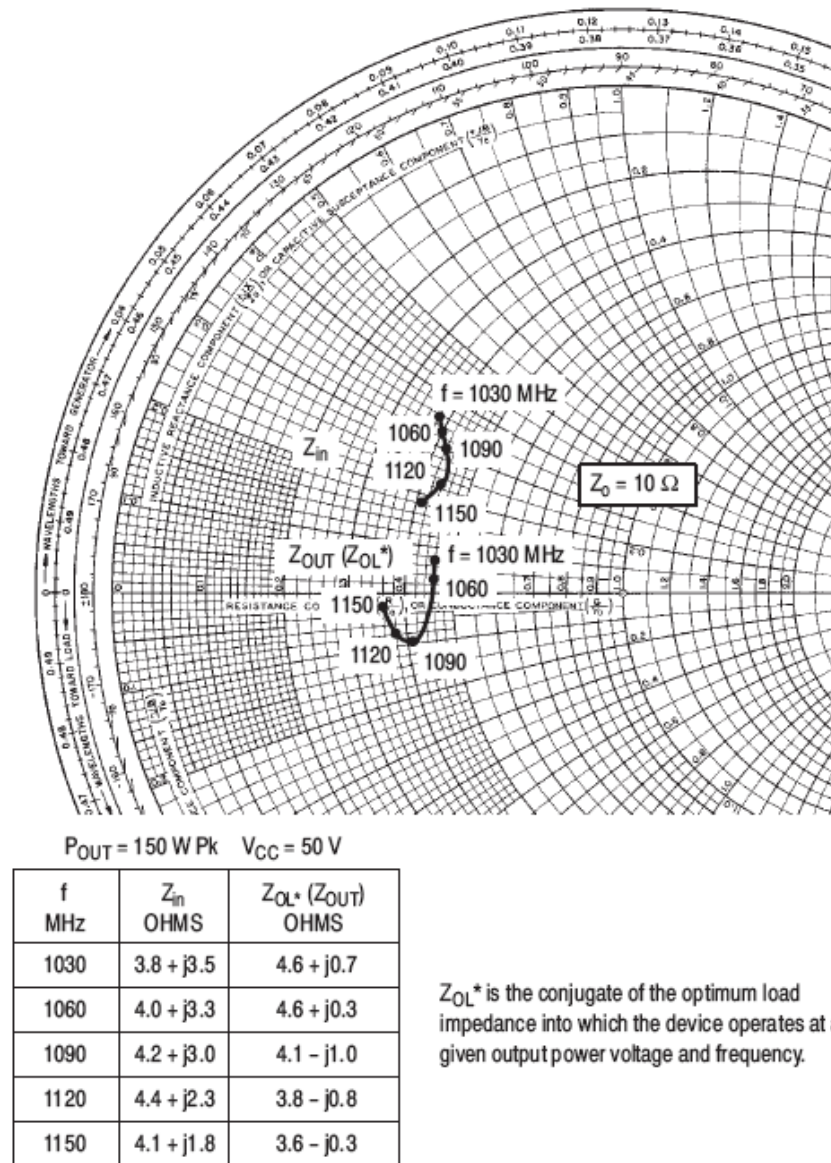
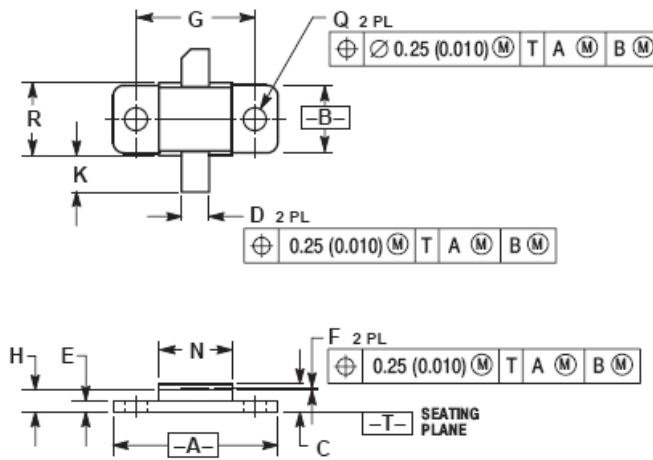


Figure 3. Series Equivalent Input/Output Impedances

Microwave Pulse Power Silicon NPN Transistor 150W (peak), 1025–1150MHz

M/A-COM Products
Released - Rev. 07.07

PACKAGE DIMENSIONS



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.890	0.910	22.61	23.17
B	0.370	0.400	9.40	10.16
C	0.145	0.160	3.69	4.06
D	0.140	0.160	3.56	4.06
E	0.055	0.065	1.40	1.65
F	0.003	0.006	0.08	0.15
G	0.050 BSC		1.61 BSC	
H	0.110	0.130	2.80	3.30
K	0.180	0.220	4.57	5.59
N	0.390	0.410	9.91	10.41
Q	0.115	0.135	2.93	3.42
R	0.390	0.410	9.91	10.41

STYLE 1:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

CASE 376B-02
ISSUE B